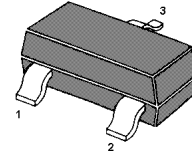
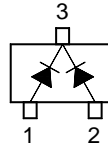


SB425D

Silicon Epitaxial Planar Schottky Barrier Diode

Low current rectification



Marking Code: "YA"
SOT-23 Plastic Package

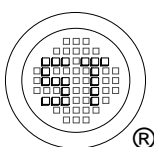
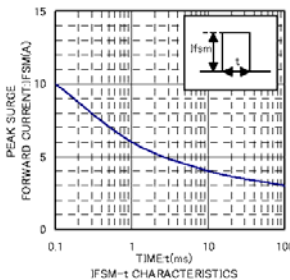
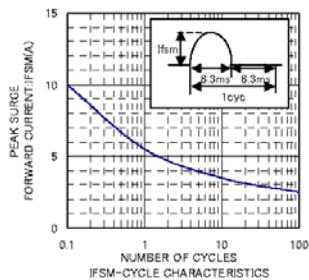
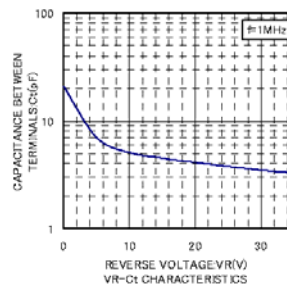
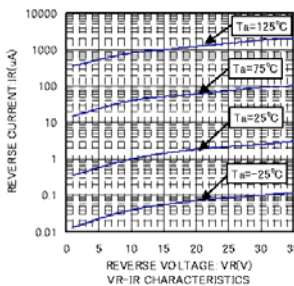
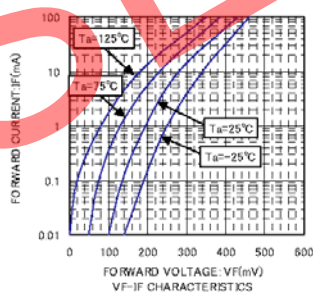
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	40	V
Average Rectified Forward Current ¹⁾	$I_{F(AV)}$	100	mA
Peak Forward Surge Current (60 Hz 1 Cycle) ¹⁾	I_{FSM}	1	A
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

¹⁾ Rating of per diode

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$ at $I_F = 100\text{ mA}$	V_F	-	0.34 0.55	V
Reverse Current at $V_R = 10\text{ V}$	I_R	-	30	μA
Capacitance between Terminals at $V_R = 10\text{ V}$, $f = 1\text{ MHz}$	C_t	6	-	pF



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Dated : 04/08/2007